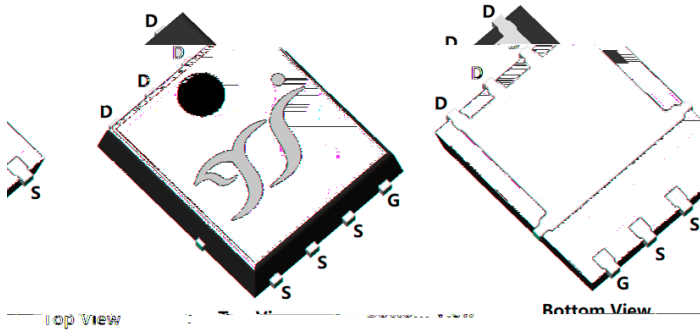


## N-Channel Enhancement Mode Field Effect Transistor



### Product Summary

- $V_{DS}$  120V
- $I_D$  88A
- $R_{DS(ON)}$  ( at  $V_{GS}=10V$ ) 7.6mohm
- $R_{DS(ON)}$  ( at  $V_{GS}=4.5V$ ) 9.6mohm
- 100% EAS Tested
- 100%  $\nabla V_{DS}$  Tested

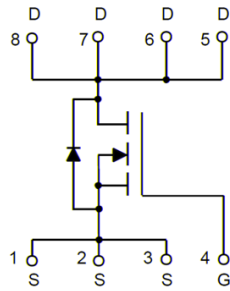
### General Description

- Split gate trench MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low  $R_{DS(ON)}$
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

### Applications

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

DFN5060-8L



PI

### ■ Absolute Maximum Ratings ( $T_A=25$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		$V_{DS}$	120	V
Gate-source Voltage		$V_{GS}$	$\pm 20$	V
Drain Current	$T_C=25^\circ C$	$I_D$	88	A
	$T_C=100^\circ C$		56	
Pulsed Drain Current <sup>A</sup>		$I_{DM}$	352	A
Avalanche energy <sup>B</sup>		EAS	400	mJ
Total Power Dissipation <sup>C</sup>	$T_C=25^\circ C$	$P_D$	120	W
	$T_C=100^\circ C$		48	
Junction and Storage Temperature Range		$T_J, T_{STG}$	-55 +150	$^\circ C$

### ■ Thermal resistance

Parameter		Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient <sup>D</sup>	$t \leq 10S$	$R_{\theta JA}$	15	20	$^\circ C/W$
	Steady-State		40	50	
Thermal Resistance Junction-to-Case	Steady-State	$R_{\theta JC}$	0.84	1.04	

### ■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJG88G12A	F1	YJG88G12A	5000	10000	100000	13" reel



# YJG88G12A

## ■ Electrical Characteristics (T<sub>J</sub>=25 unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
<b>Static Parameter</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> =250μA	120	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =120V, V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> =0V	-	-	±100	nA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> =250μA	1.0	2.0	3.0	V
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =20A	-	6.4	7.6	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =20A	-	7.6	9.6	mΩ
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =20A, V <sub>GS</sub> =0V	-	-	1.3	V
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =5V, I <sub>D</sub> =20A	-	80	-	S
Gate resistance	R <sub>G</sub>	f=1MHz	-	0.9	-	Ω
Maximum Body-Diode Continuous Current	I <sub>S</sub>		-	-	88	A
<b>Dynamic Parameters</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =50V, V <sub>GS</sub> =0V, f=1MHZ	-	4619	-	pF
Output Capacitance	C <sub>oss</sub>		-	924	-	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	28	-	
<b>Switching Parameters</b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>GS</sub> =10V, V <sub>DS</sub> =50V, I <sub>D</sub> =20A	-	72.0	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	19.5	-	
Gate-Drain Charge	Q <sub>gd</sub>		-	8.2	-	
Reverse Recovery Charge	Q <sub>rr</sub>	I <sub>F</sub> =20A, di/dt=100A/us	-	195	-	nC
Reverse Recovery Time	t <sub>rr</sub>		-	86	-	
Turn-on Delay Time	t <sub>D(on)</sub>	V <sub>GS</sub> =10V, V <sub>DD</sub> =50V, I <sub>D</sub> =20A R <sub>GEN</sub> =2.2Ω	-	19	-	ns
Turn-on Rise Time	t <sub>r</sub>		-	36	-	
Turn-off Delay Time	t <sub>D(off)</sub>		-	45	-	
Turn-off fall Time	t <sub>f</sub>		-	45	-	

A. Repetitive rating; pulse width limited by max. junction temperature.

B. T<sub>J</sub>=25°C, V<sub>DD</sub>=50V, V<sub>G</sub>=10V, R<sub>G</sub>=25Ω, L=2mH, I<sub>AS</sub>=20A

C. P<sub>d</sub> is based on max. junction temperature, using junction-case thermal resistance.

D. The value of R<sub>θJA</sub> is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25°C. The Power dissipation PDSM is based on R<sub>θJA</sub> ≤ 10s and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.



## ■ Typical Performance Characteristics

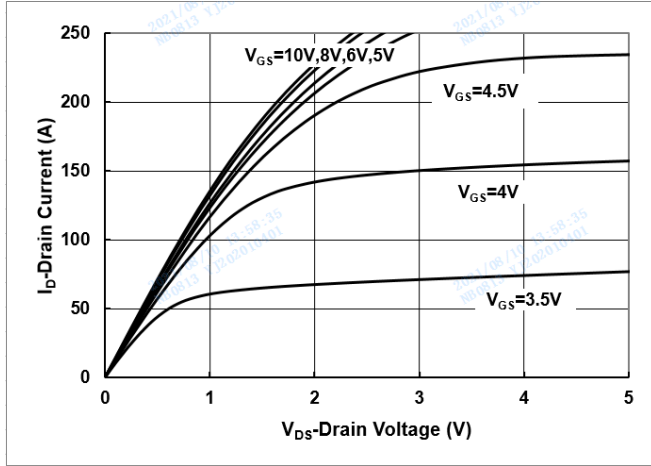


Figure1. Output Characteristics

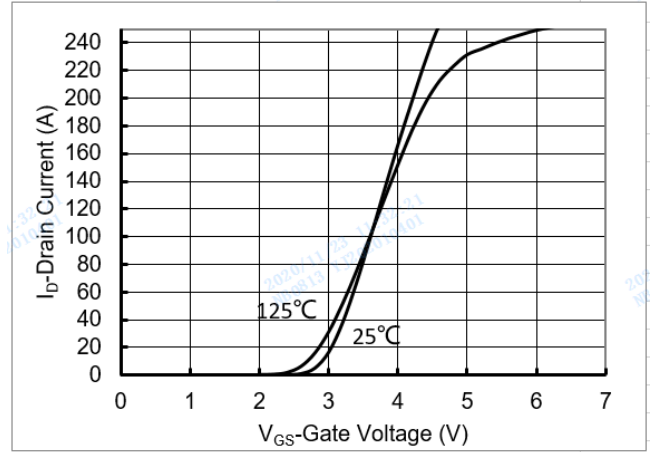


Figure2. Transfer Characteristics

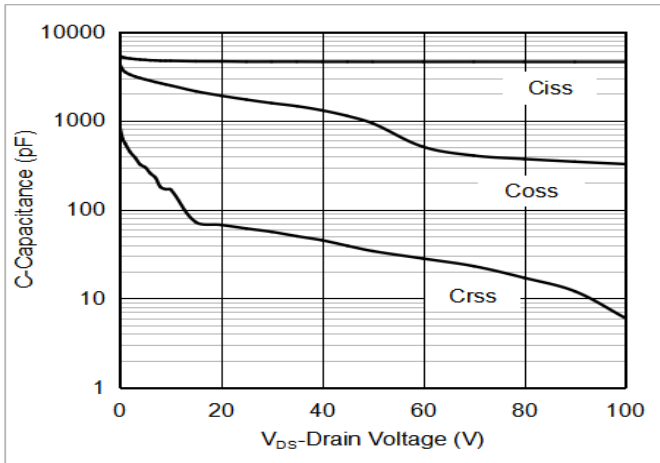


Figure3. Capacitance Characteristics

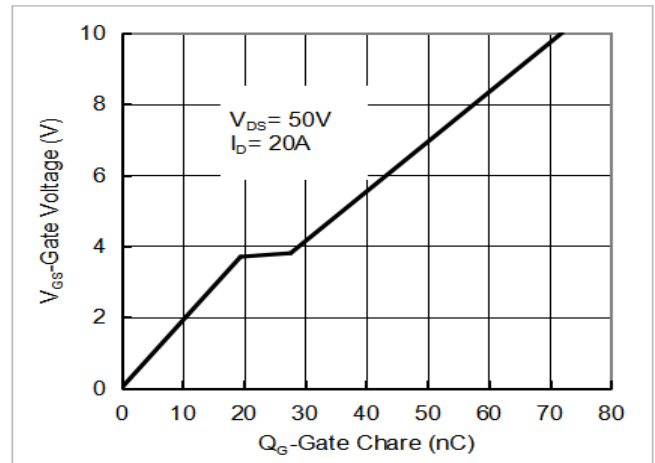


Figure4. Gate Charge

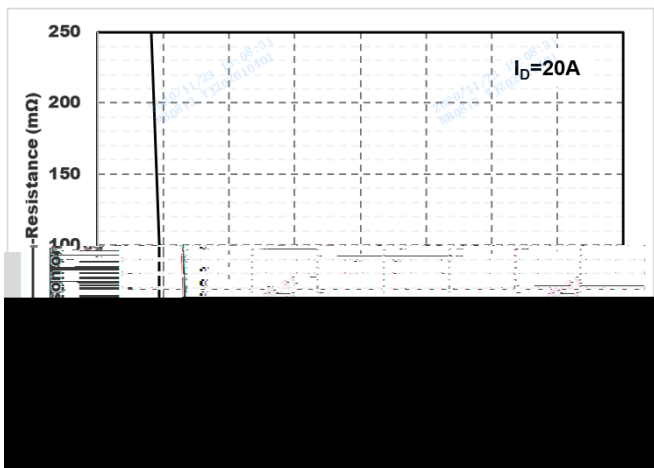


Figure5. : On-Resistance vs. Gate to Source Voltage

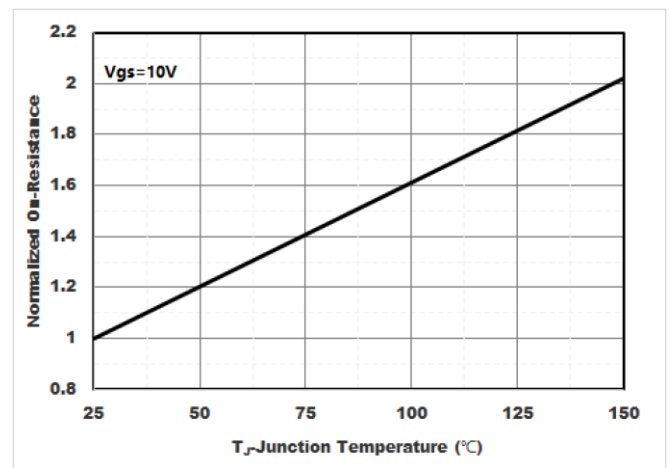


Figure6. Normalized On-Resistance

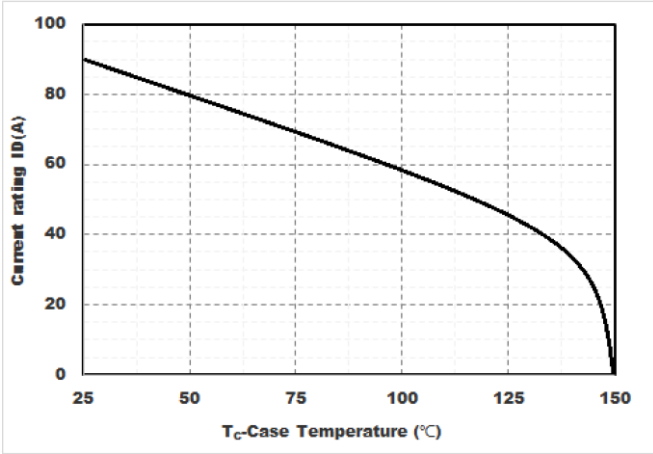


Figure7. Drain current

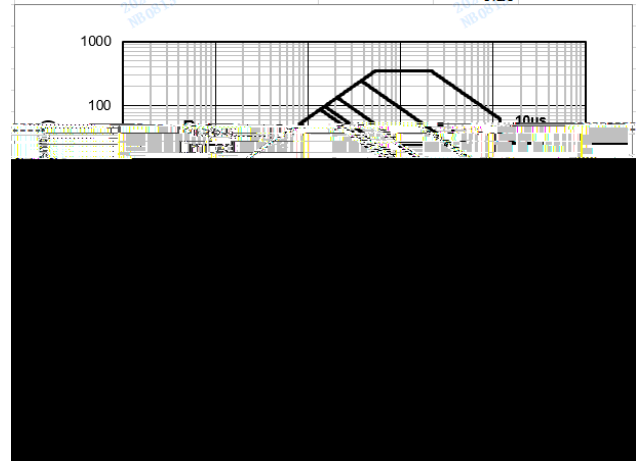


Figure8.Safe Operation Area

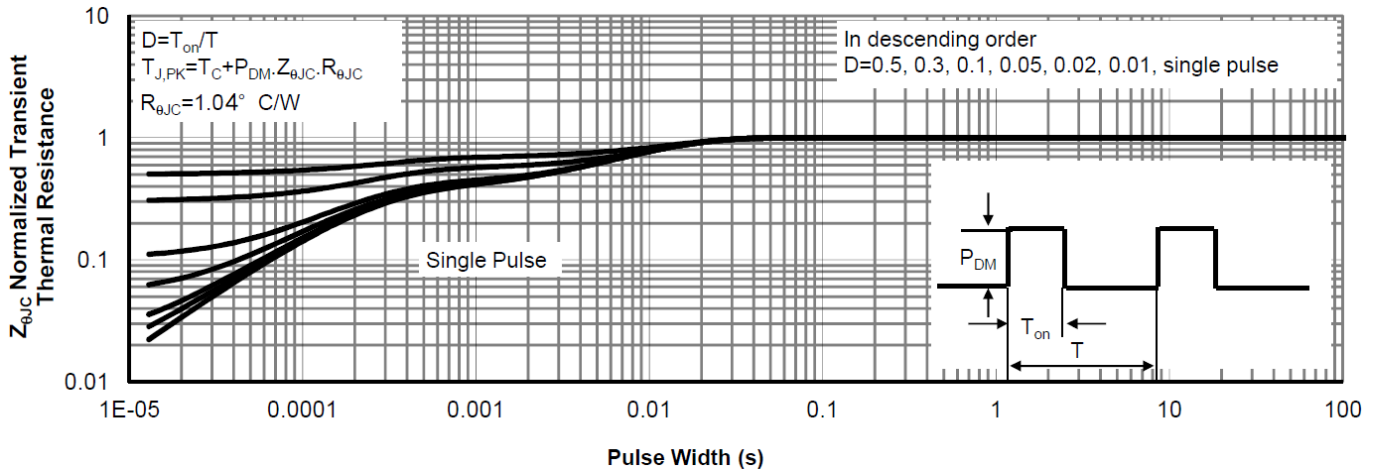
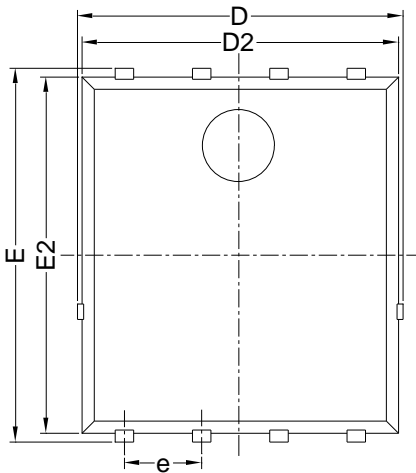


Figure9. Normalized Maximum Transient thermal impedance

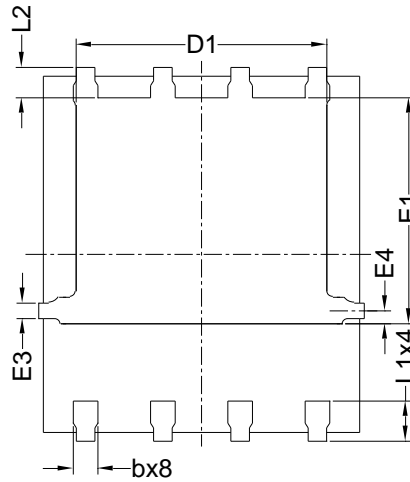


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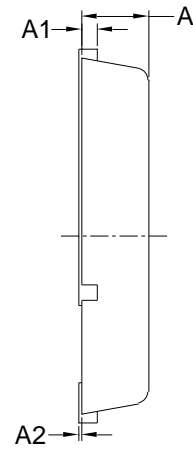
## ■ PDFN5060-8L-B-1.1MM Package information



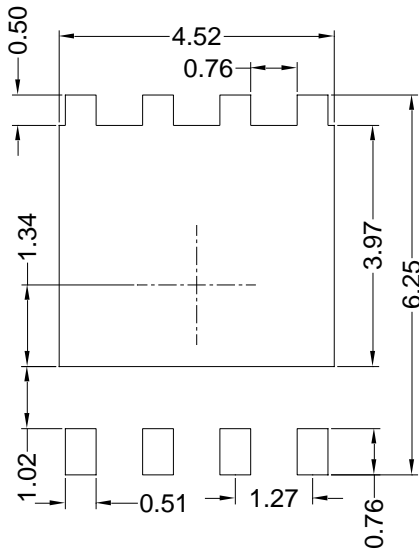
Top View



Bottom View



Side View



Suggested Solder Pad Layout  
Top View

SYMBOL	MILLIMETER		
	MIN	NOM	MAX
D	5.15	5.35	5.55
E	5.95	6.15	6.35
A	1.00	1.10	1.20
A1	0.254 BSC		
A2			0.10
D1	3.92	4.12	4.32
E1	3.52	3.72	3.92
D2	5.00	5.20	5.40
E2	5.66	5.86	6.06
E3	0.254 REF		
E4	0.21 REF		
L1	0.56	0.66	0.76
L2	0.50 BSC		
b	0.31	0.41	0.51
e	1.27 BSC		

Note:

1. Controlling dimension: in millimeters.
2. General tolerance:  $\pm 0.10$ mm.
3. The pad layout is for reference purposes only.



# YJG88G12A

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